(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
2 March 2006 (02.03.2006)

PCT

(10) International Publication Number
WO 2006/023428 A2

(51) International Patent Classification:
H01L 27/146 (2006.01)

(21) International Application Number:
PCT/US2005/028913

(22) International Filing Date: 15 August 2005 (15.08.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/923,692 24 August 2004 (24.08.2004) US

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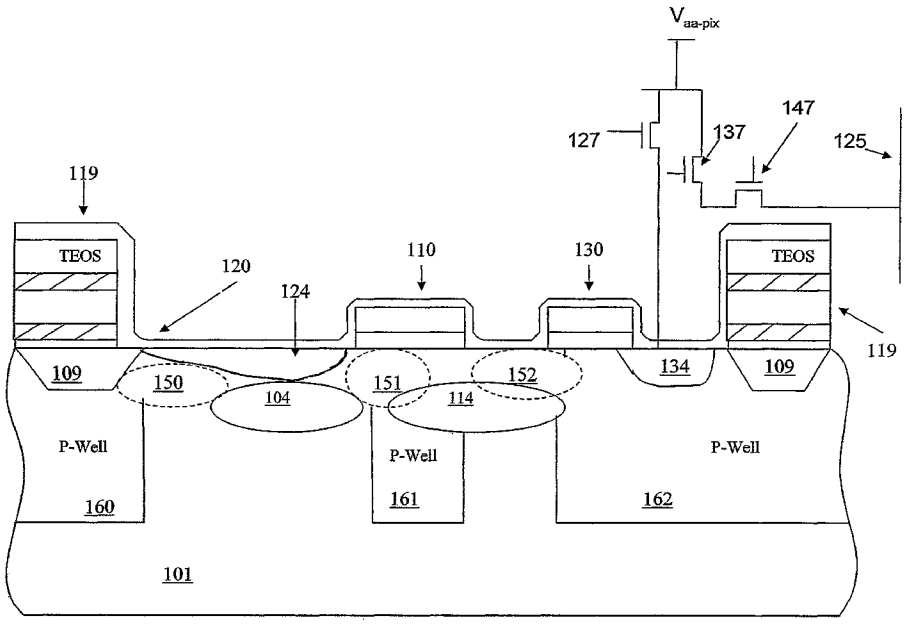
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *without international search report and to be republished upon receipt of that report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) **Title:** METHOD OF FABRICATING A STORAGE GATE PIXEL DESIGN



(57) **Abstract:** A method of fabricating a pixel cell having a shutter gate structure. First and second charge barriers are respectively created between a photodiode and a first charge storage region and between the first storage region and a floating diffusion region. A global shutter gate is formed to control the charge barrier and transfer charges from the photodiode to the first charge storage region by effectively lowering the first charge barrier. A transfer transistor acts to transfer charges from the first storage region to the floating diffusion region by reducing the second charge barrier.

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